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Family Name					
Given Name/s					
Student Number					
Teaching Period	Semester 1, 2019				

ENG221 – Analogue Electronics	DURATION	
	Reading Time:	10 minutes
	Writing Time:	180 minutes
INSTRUCTIONS TO CANDIDATES		
<ul style="list-style-type: none"> • Exam has five questions. • Answer all questions of the exam. • Exam has 60 marks. 		
EXAM CONDITIONS		
<p><u>You may begin writing from the commencement of the examination session.</u> The reading time indicated above is provided as a guide only.</p>		
This is a CLOSED BOOK examination		
Any non-programmable calculator is permitted		
No handwritten notes are permitted		
No dictionaries are permitted		
ADDITIONAL AUTHORISED MATERIALS	EXAMINATION MATERIALS TO BE SUPPLIED	
No additional printed material is permitted	1 x 20 Page Book 1 x Scrap Paper Formula Sheet/s	

**THIS EXAMINATION IS PRINTED
DOUBLE-SIDED.**

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LEFT BLANK.**

Question 1 (14 marks)

For the amplifier shown in Figure 1, answer the following questions:

- Determine the DC Drain current value of the circuit. (3 marks)
- Determine the input resistance of the amplifier (R_{in}). (2 marks)
- Determine the output resistance of the amplifier (R_{out}). (4 marks)
- Determine the overall voltage gain of the amplifier (V_o/V_{sig}). (5 marks)

Assume,

$R_{sig}=100\text{K}\Omega$, $R_G=1\text{M}\Omega$, $R_S=4\text{K}\Omega$, $R_L=4\text{K}\Omega$, $V_t=1\text{V}$, $K'_n(W/L)=2\text{ mA/V}^2$ and $|V_A|=50\text{ V}$.

$V_{DD}=10\text{ V}$, $V_{SS}=-10\text{V}$.

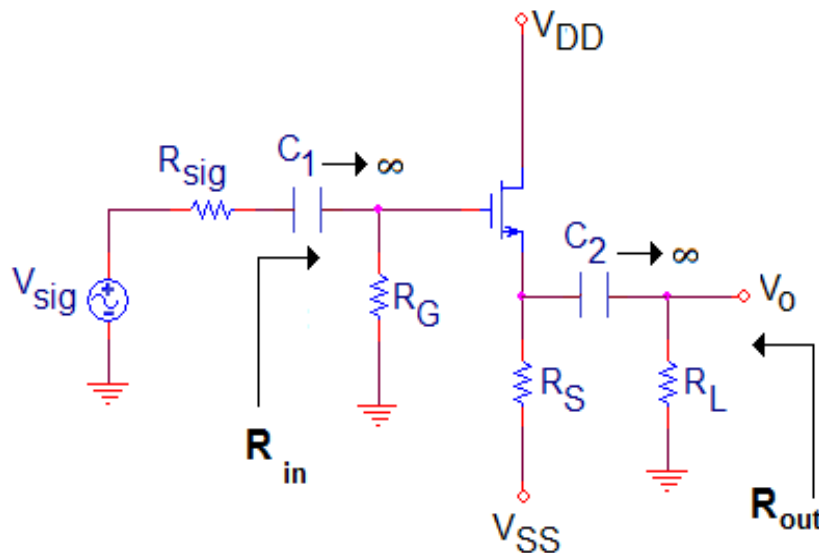


Figure 1.

Question 2 (9 marks)

For the NMOS-based amplifier shown in Figure 2, answer the following questions:

- Determine the input resistance of the amplifier (R_{in}). (1 marks)
- Determine the output resistance of the amplifier (R_{out}). (2 marks)
- Determine the overall voltage gain of the amplifier (V_o/V_{sig}). (4 marks)
- By what factor should the bias current (I_D) of the MOSFET be changed to have $R_{in}=R_{sig}$? (2 marks)

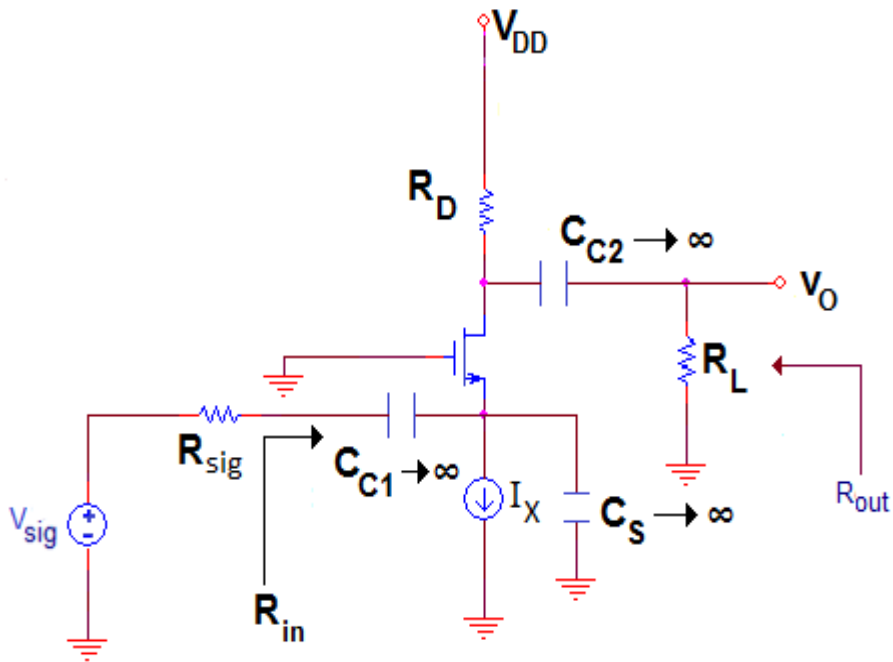


Figure 2.

Assume,

$$R_{sig}=500\Omega, R_D=10\text{ K}\Omega, R_L=10\text{ K}\Omega, g_m=1\text{ mA/V}^2.$$

Ignore the Early effect.

Question 3 (5 marks)

For the circuit shown in Figure 3, determine the minimum value of R_E to maintain the transistor in the active region.

Assume, $R_B=7K\Omega$, $R_C=3K\Omega$, $V_{CC}= -10V$, $\beta=100$, $V_{EC(sat)}=0.2V$.

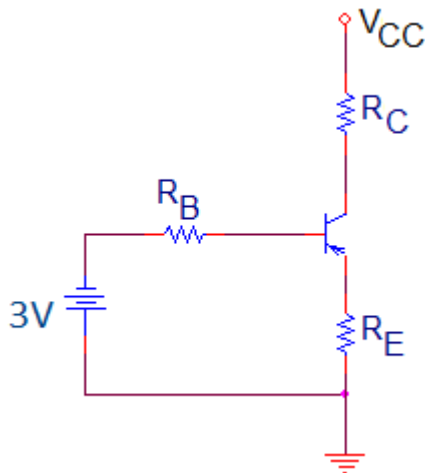


Figure 3.

Question 4 (17 marks)

For the circuit shown in Figure 4, answer the following questions:

- Determine the DC emitter current value of the circuit. (4 marks)
- Draw the small-signal model of the circuit (based on π or T model of transistor equivalent circuit). (4marks)
- Based on the circuit drawn in part (b), determine the overall voltage gain (V_o/V_{sig}) of the amplifier. (6 marks)
- Based on the circuit drawn in part (b), determine the input resistance of the amplifier. (3 marks)

Assume, $R_1=120\text{ K}\Omega$, $R_2=500\text{ K}\Omega$, $R_3=500\text{K}\Omega$, $R_4=3\text{ K}\Omega$, $R_5=R_L=1\text{K}\Omega$ and $\beta=100$.

Ignore the Early effect.

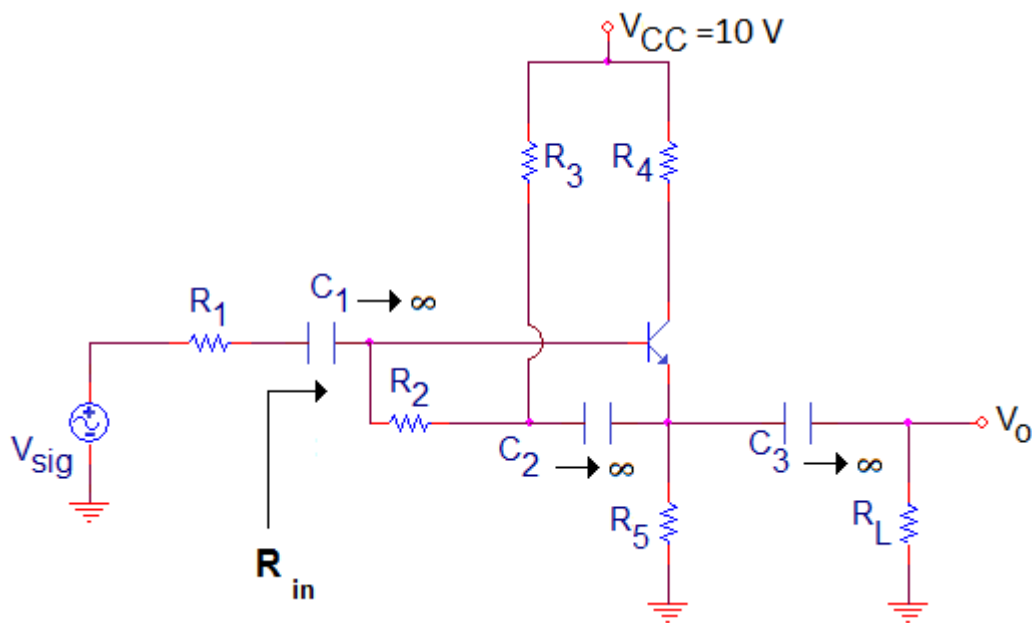


Figure 4.

Question 5 (15 marks)

For the circuit shown in Figure 5, answer the following questions:

- Determine the DC emitter current value of the circuit. (4 marks)
- Draw the small-signal model of the circuit (based on π or T model of transistor equivalent circuit). (3 marks)
- Based on the circuit drawn in part (b), determine the overall voltage gain of the amplifier (V_o/V_{sig}). (8 marks)

Assume $V_{CC}=10V$, $R_1=300K\Omega$, $R_2=10K\Omega$, $R_E=100\Omega$, $R_{sig}=15K\Omega$, $\beta=100$.

Ignore the Early effect.

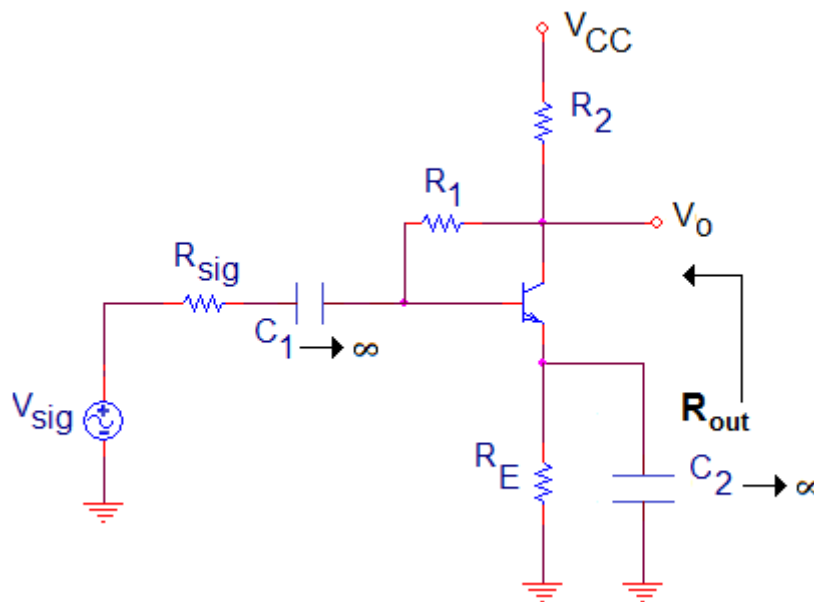


Figure 5.

Formula sheet

$$i_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (v_{GS} - V_t)^2 \left(1 + \frac{v_{DS}}{V_A}\right) = \frac{1}{2} k'_n \frac{W}{L} (v_{GS} - V_t)^2 \left(1 + \frac{v_{DS}}{V_A}\right)$$

NMOSFET

$$g_m = (\mu_n C_{ox}) \left(\frac{W}{L}\right) V_{OV} = \sqrt{2(\mu_n C_{ox}) \left(\frac{W}{L}\right) I_D}$$

$$r_o = \frac{V_A}{I_D}$$

$$V_A = \frac{1}{\lambda} \quad g_m = \frac{I}{V_{OV}/2}$$

PMOSFET

$$i_D = \frac{1}{2} \mu_p C_{ox} \frac{W}{L} (v_{SG} - |V_t|)^2 \left(1 + \frac{v_{SD}}{V_A}\right) = \frac{1}{2} k'_p \frac{W}{L} (v_{SG} - |V_t|)^2 \left(1 + \frac{v_{SD}}{V_A}\right)$$

$$g_m = (\mu_p C_{ox}) \left(\frac{W}{L}\right) V_{OV} = \sqrt{2(\mu_p C_{ox}) \left(\frac{W}{L}\right) I_D}$$

$$r_o = \frac{|V_A|}{I_D}$$

$$V_A = \frac{1}{\lambda}$$

BJT

$$i_C = I_S e^{v_{BE}/V_T} \left(1 + \frac{v_{CE}}{V_A}\right)$$

$$i_B = \frac{i_C}{\beta} \quad \Delta I_B = \frac{\Delta I_C}{\beta}$$

$$g_m = \frac{I_C}{V_T}$$

$$g_m r_e = \alpha$$

$$\alpha = \frac{\beta}{\beta + 1}$$

$$r_\pi = \frac{\beta}{g_m}$$

$$r_o = \frac{V_A}{I_C}$$

$$V_T = 25 \text{ mV} \quad V_{BE} = 0.7 \text{ V}$$